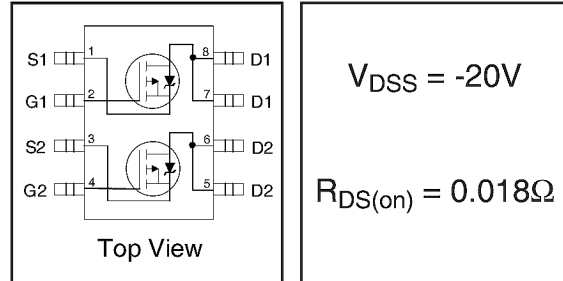


# IRF7324PbF

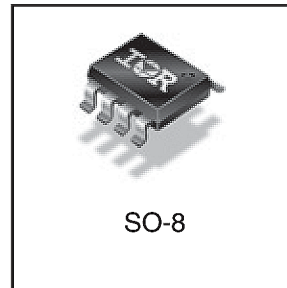
HEXFET® Power MOSFET

- Trench Technology
- Ultra Low On-Resistance
- Dual P-Channel MOSFET
- Low Profile (<1.1mm)
- Available in Tape & Reel
- 2.5V Rated
- Lead-Free



## Description

New trench HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in battery and load management applications.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-9.0	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-7.1	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	-71	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation <sup>③</sup>	2.0	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation <sup>③</sup>	1.3	W
	Linear Derating Factor	16	mW/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

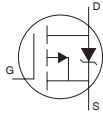
## Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient <sup>③</sup>	62.5	°C/W

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.02	—	V/°C	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.018	$\Omega$	$V_{GS} = -4.5V, I_D = -9.0A$ ②
		—	—	0.026		$V_{GS} = -2.5V, I_D = -7.7A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.45	—	-1.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$g_{fs}$	Forward Transconductance	19	—	—	S	$V_{DS} = -10V, I_D = -9.0A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-1.0	$\mu A$	$V_{DS} = -16V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -12V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 12V$
$Q_g$	Total Gate Charge	—	42	63	nC	$I_D = -9.0A$
$Q_{gs}$	Gate-to-Source Charge	—	7.1	11		$V_{DS} = -16V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	12	18		$V_{GS} = -5.0V$
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD} = -10V$
$t_r$	Rise Time	—	36	—		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	170	—		$R_G = 6.0\Omega$
$t_f$	Fall Time	—	190	—		$R_D = 10\Omega$ ②
$C_{iss}$	Input Capacitance	—	2940	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	630	—		$V_{DS} = -15V$
$C_{rss}$	Reverse Transfer Capacitance	—	420	—		$f = 1.0\text{MHz}$

## Source-Drain Ratings and Characteristics

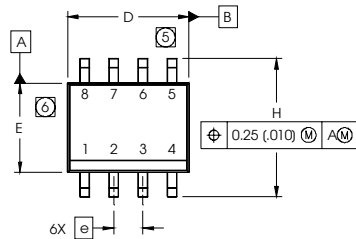
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-7.1		
$V_{SD}$	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -2.0A, V_{GS} = 0V$ ②
$t_{rr}$	Reverse Recovery Time	—	180	270	ns	$T_J = 25^\circ\text{C}, I_F = -2.0A$
$Q_{rr}$	Reverse Recovery Charge	—	300	450	nC	$di/dt = -100A/\mu s$ ②

### Notes:

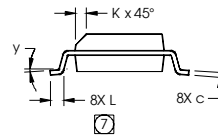
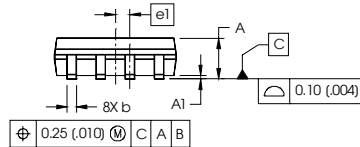
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .
- ③ Surface mounted on FR-4 board,  $t \leq 10\text{sec}$ .

## SO-8 Package Outline

Dimensions are shown in millimeters (inches)



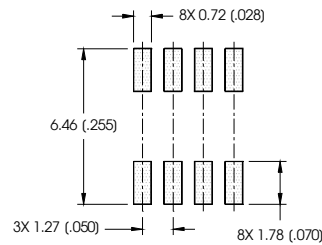
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



**NOTES:**

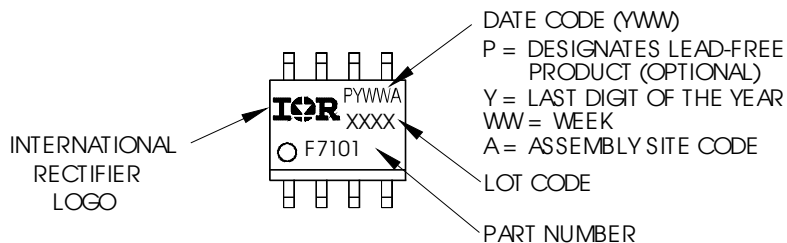
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

**FOOTPRINT**



## SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

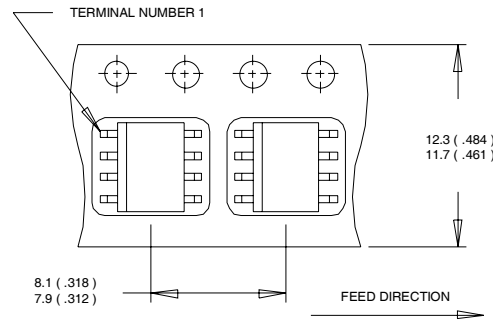


# IRF7324PbF

International  
**IR** Rectifier

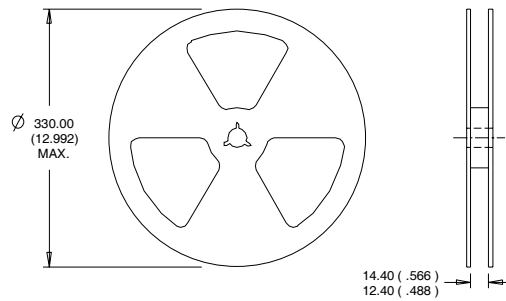
## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualifications Standards can be found on IR's Web site.

International  
**IR** Rectifier